## P-Channel 60-V (D-S) MOSFET

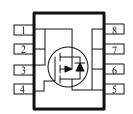
These miniature surface mount MOSFETs utilize High Cell Density process. Low r<sub>DS(on)</sub> assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

•	Low r <sub>DS(on)</sub> Provides Higher Efficiency and
	Extends Battery Life

- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (±25) for battery pack applications

PRODUCT SUMMARY				
$V_{DS}(V)$ $r_{DS(on)} m(\Omega)$ $I_D(A)$				
-60	$17 @ V_{GS} = -10V$	-9.3		
-00	$23 @ V_{GS} = -4.5V$	-8.0		





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage			-60	V	
Gate-Source Voltage			±20	V	
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$		±9.3		
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	±8.0	A	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	±30			
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	-2.5	A	
D D: a	$T_A=25^{\circ}C$	$D_{-}$	3.1	W	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	L D	2.0		
Operating Junction and Storage Temperature Range		$T_{J}, T_{stg}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	50	°C/W	

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM4417P

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	Limits			Unit	
i ai ametei	Symbol	Symbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1				
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \ V, \ V_{GS} = \pm 20 \ V$			±100	nA	
Zero Gate Voltage Drain Current	$I_{ m DSS}$	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	1DSS	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-20			Α	
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = -10 \text{ V}, I_D = -9.3 \text{ A}$			17	mΩ	
Drain-Source On-Resistance	$r_{\mathrm{DS(on)}}$	$V_{GS} = -4.5 \text{ V}, I_D = -8.0 \text{ A}$			23		
Forward Tranconductance <sup>A</sup>	$\mathbf{g}_{\mathrm{fs}}$	$V_{DS} = -15 \text{ V}, I_D = -9.3 \text{ A}$		8		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = -2.5 \text{ A}, V_{GS} = 0 \text{ V}$			-1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		121			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -8.0 \text{ A}$		20.0		пC	
Gate-Drain Charge	$Q_{gd}$	I <sub>D</sub> = -0.0 A		32.0			
Turn-On Delay Time	$t_{d(on)}$			20			
Rise Time	$t_{\rm r}$	$V_{DD} =$ -30 V, $R_L = 30 \; \Omega$ , $I_D =$ -1 A,		20		nS	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V},  R_G = 6\Omega$		205		1113	
Fall-Time	$t_{\mathrm{f}}$			90			

## Notes

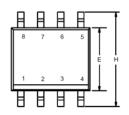
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

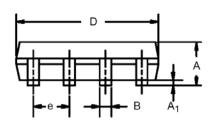
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## Package Information

SO-8: 8LEAD

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	MILLIN	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC 0.050 BSC			BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	

